PRESS RELEASE

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InnoScience powers GaN device development with multiple AIXTRON MOCVD systems

AIX G5+ C high-volume manufacturing platform paves way to high-performing 650V GaN-on-Si[1] devices

Herzogenrath/Germany, November 21, 2018 – AIXTRON SE (FSE: AIXA), a worldwide leading provider of deposition equipment to the semiconductor industry, will deliver multiple AIX G5+ C MOCVD systems to InnoScience Technology Co., Ltd. (China) for the development of GaN (gallium nitride) power devices which are more and more favored over Si (silicon) power devices in various applications due to their superior performance at high frequency. All AIXTRON cluster tools will feature a 5x200 mm configuration and will be shipped until Q2/2019.

GaN power devices have very low conduction loss, switching loss and off state loss compared to the traditional Si-based power chips due to a higher breakdown strength, faster switching speed, higher thermal conductivity and lower on-resistance. GaN power devices are being used already today for applications such as efficient power supplies for PC and servers or LiDAR (*Light Detection And Ranging*) and wireless power transfer requiring high-speed switching higher than 1 MHz. In addition, they also have advantages for electric vehicles applications like On-Board Chargers (OBC) because of significantly reduced system size by superior thermal properties and reduction of the passive components.

In the scope of the increasing number of applications, AIXTRONs AIX G5+ C platform can play out its advantages in the manufacturing process since the system allows for scalable processes, tight uniformity and particle control of the epitaxial wafers to enable highest yield and maximum throughput at the lowest cost of ownership.

Jay Son, CEO of InnoScience Technology, says: "We have chosen the AIX G5+ C as it has proven to provide excellent thickness and wafer uniformity due to the superior capabilities of the Planetary® batch reactor concept. The newly acquired systems will enable us to ramp up manufacturing of our high-end products such as 650V GaN-on-Si devices with the best cost per wafer in the market."

"Market demand for power electronics, especially for GaN-based devices is picking up speed with AIXTRON having the most capable system available in the market. We are pleased that InnoScience leads the way in China and has decided to select this system which convinces not only by performance but also by making the production of GaN power devices commercially viable," comments Dr. Felix Grawert, President of AIXTRON SE.

[1] *GaN-on-Si = Gallium Nitride-on-Silicon*

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About AIXTRON
AIXTRON SE is a leading provider of deposition equipment to the semiconductor industry. The Company was founded in 1983 and is headquartered in Herzogenrath (near Aachen), Germany, with subsidiaries and sales offices in Asia, United States and in Europe. AIXTRON´s technology solutions are used by a diverse range of customers worldwide to build advanced components for electronic and opto-electronic applications based on compound or organic semiconductor materials. Such components are used in a broad range of innovative applications, technologies and industries. These include Laser and LED applications, display technologies, data transmission, SiC and GaN power management and conversion, communication, signaling and lighting as well as a range of other leading-edge technologies.

Our registered trademarks: AIXACT®, AIXTRON®, APEVA®, Atomic Level SolutionS®, Close Coupled Showerhead®, CRIUS®, EXP®, EPISON®, Gas Foil Rotation®, Optacap™, OVPD®, Planetary Reactor®, PVPD®, STExS®, TriJet®

For further information on AIXTRON (FSE: AIXA, ISIN DE000A0WMPJ6) please visit our website at: www.aixtron.com.

About Innoscience Technology
Innoscience Technology Co., Ltd. was co-founded in December 2015 by scientists and experts from the U.S., Korea, Taiwan, and China. Innoscience is devoted to the R&D and manufacture of wide-bandgap semiconductors. The first fab is located in Zhuhai National Hi-Tech District (China). Innoscience has established China's first mass production line of 8-inch E-mode GaN-on-Si power devices. The key products include 30V-650V GaN-on-Si power devices. The product's design and performance have reached the world advanced level. Innoscience aims to build a world leading company in power devices in China and is committed to devote to China's semiconductor industry.

Forward-Looking Statements
This document may contain forward-looking statements regarding the business, results of operations, financial condition and earnings outlook of AIXTRON. These statements may be identified by words such as "may", "will", "expect", "anticipate", "contemplate", "intend", "plan", "believe", "continue" and "estimate" and variations of such words or similar expressions. These forward-looking statements are based on our current assessments, expectations and assumptions, of which many are beyond control of AIXTRON, and are subject to risks and uncertainties. You should not place undue reliance on these forward-looking statements. Should these risks or uncertainties materialize, or should underlying expectations not occur or assumptions prove incorrect, actual results, performance or achievements of AIXTRON may materially vary from those described explicitly or implicitly in the relevant forward-looking statement. This could result from a variety of factors, such as actual customer orders received by AIXTRON, the level of demand for deposition technology in the market, the timing of final acceptance of products by customers, the condition of financial markets and access to financing for AIXTRON, general conditions in the market for deposition plants and macroeconomic conditions, cancellations, rescheduling or delays in product shipments, production capacity constraints, extended sales and qualification cycles, difficulties in the production process, the general development in the semi-conductor industry, increased competition, fluctuations in exchange rates, availability of public funding, fluctuations and/or changes in interest rates, delays in developing and marketing new products, a deterioration of the general economic situation and any other factors discussed in any reports or other announcements , in particular in the chapter Risks in the Annual Report, filed by AIXTRON. Any forward-looking statements contained in this document are based on current expectations and projections of the executive board based on information available the date hereof. AIXTRON undertakes no obligation to revise or update any forward-looking statements as a result of new information, future events or otherwise, unless expressly required to do so by law.

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